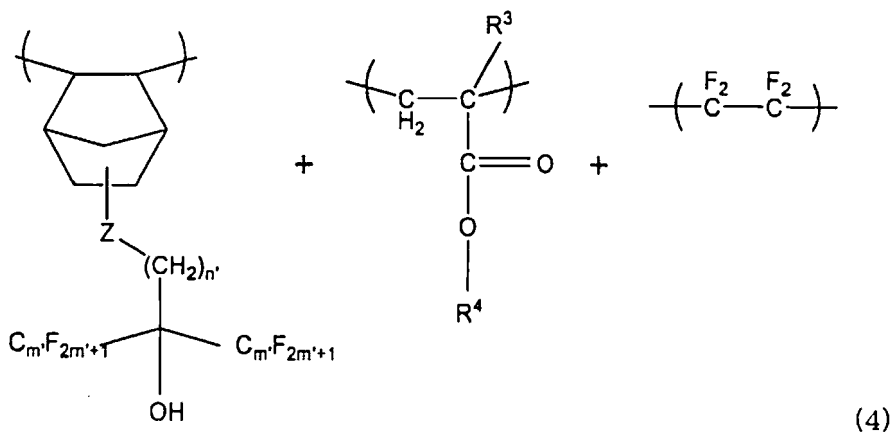
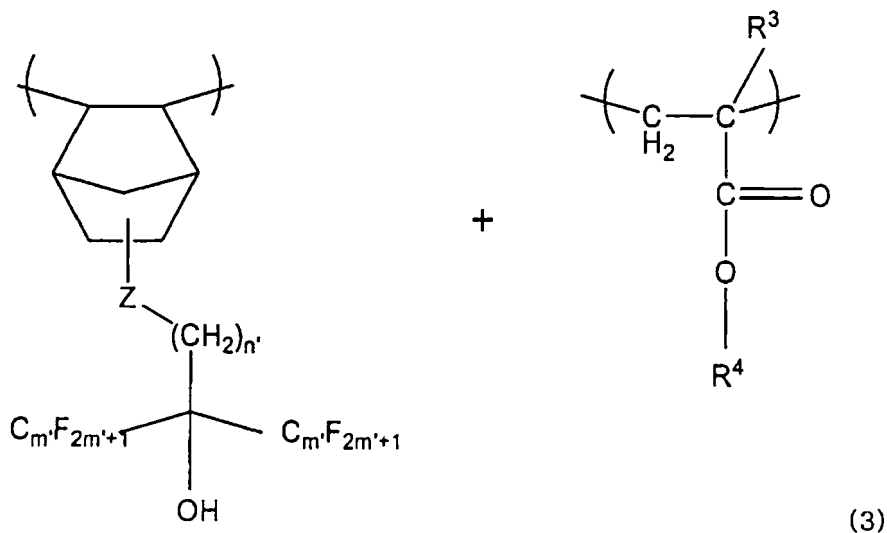
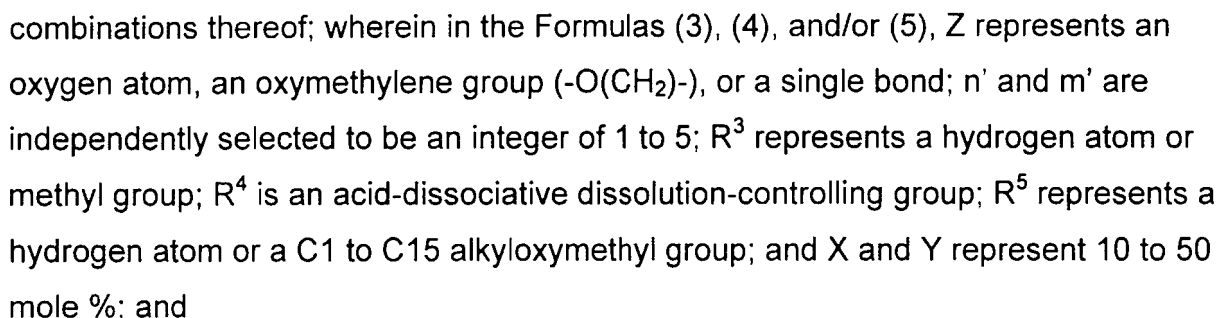


# AMENDMENTS TO THE CLAIMS

1. (previously presented) A photoresist composition comprising:

(A) a polymer component comprising an alkaline-soluble constitutional unit that contains an aliphatic cyclic group having both (i) a fluorine atom or a fluorinated alkyl group and (ii) an alcoholic hydroxide group, the alkaline solubility of the polymer component being changeable by action of an acid wherein said polymer component comprises at least one polymer selected from the group represented by the following Formulas:




$$\begin{array}{c} \text{R}^1 \\ | \\ \text{R}^2 - \text{S}^+ \\ | \\ \text{R}^3 \end{array} \quad \begin{array}{c} \text{SO}_2 \\ \diagup \quad \diagdown \\ \text{N}^- \quad \text{X} \\ \diagdown \quad \diagup \\ \text{SO}_2 \end{array} \quad (1)$$

2. (original) A photoresist composition according to claim 1, further comprising a nitrogen-containing organic compound.

3. (original) A photoresist composition according to claim 1, further comprising an organic carboxylic acid, or a phosphorous oxo acid or derivative thereof.

4. (original) A method of forming a resist pattern, comprising:  
  
coating the photoresist composition according to claim 1 on a substrate to form a resist film,  
  
selectively exposing the resist film, and  
  
heating and developing the resist film after exposure to form a resist pattern.

5. (original) A method of forming a resist pattern according to claim 4, wherein a SiON film is provided on the substrate.